

# BAX12/BAX12A CONTROLLED AVALANCHE DIODES

## DO-35(GLASS)

1.0 2(26.0)

## Features

- Switching speed: max. 50 ns
- Continuous reverse voltage: max. 90V
- Repetitive peak reverse voltage: max. 90V
- Repetitive peak forward current: max.800 mA
- Repetitive peak reverse current: max.600mA

## **Mechanical Data**

- Case : DO-35 Glass Case
- Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 0.13 gram (approximately)



# $\begin{array}{c} 0.079(2.0) \\ \hline MAX \end{array} \\ \hline \\ 0.165 (4.2) \\ \hline \\ MAX \\ \hline \\ 0.165 (4.2) \\ \hline \\ MAX \\ \hline \\ \hline \\ 0.020(0.52) \\ \hline \\ TYP \end{array} \\ \hline \\ \hline \\ \hline \\ \hline \\ \end{array}$



Dimensions in millimeters

### **Maximum Ratings** @ $T_A = 25^{\circ}C$ unless otherwise specified

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V <sub>RRM</sub>	90	V
Continuous Reverse Voltage		V <sub>R</sub>	90	V
Continuous Forward Current		I <sub>F</sub>	400	mA
Repetitive Peak Forward Current		I <sub>FRM</sub>	800	A
Non-repetitive Peak Forward Current	t = 1 µs		55	
Square wave: Tj = 25 °C prior to surge	t = 100 µs	I <sub>FSM</sub>	15	A
	t = 10 ms		9	
Total Power Dissipation , Ta = 25 °C		P <sub>tot</sub>	450	mW
Repetitive Peak Reverse Current		I <sub>RRM</sub>	600	mA
Junction Temperature		TJ	200	°C
Storage Temperature Range		T <sub>S</sub>	-65 to + 200	°C

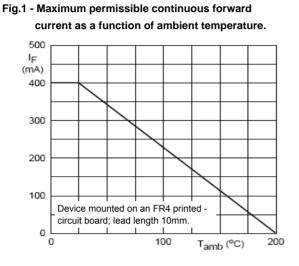
Note : (1) Device mounted on an FR4 printed circuit-board; lead length 10 mm.

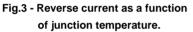
## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Test Condition	Min.	Max.	Unit
Reverse Avalanche	BAX12	V	I <sub>R</sub> = 1mA	120	170	V
Breakdown Voltage	BAX12A	V <sub>(BR)R</sub>	I <sub>R</sub> = 0.1mA	120	170	V
Reverse Current		I <sub>R</sub>	V <sub>R</sub> = 90 V	-	100	nA
			V <sub>R</sub> = 90 V, Tj = 150 °C	-	100	μA
Forward Voltage		V <sub>F</sub>	I <sub>F</sub> = 400 mA	-	1.25	V
Diode Capacitance		Cd	f = 1MHz ; V <sub>R</sub> = 0	-	35	pF
			I <sub>F</sub> = 30mA , I <sub>R</sub> = 30mA			
Reverse Recovery Time		Trr	$R_L$ = 100 $\Omega$ measured at	-	50	ns
			I <sub>R</sub> = 3 mA			



# RATING AND CHARACTERISTIC CURVES (BAX12, BAX12A)





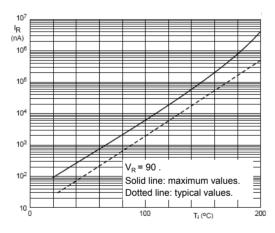


Fig.2 - Forward current as a function of forward voltage.

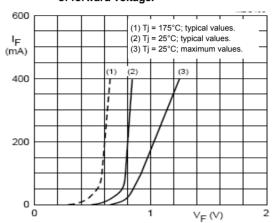


Fig.4 - Diode capacitance as a function of reverse voltage; typical values.

